

CEPF630/CEBF630

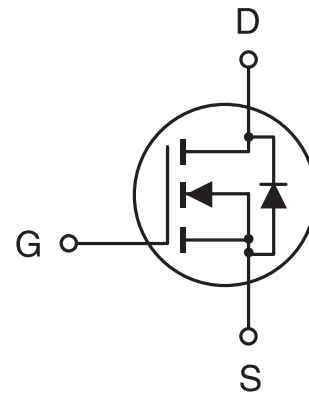
March 1998

N-Channel Enhancement Mode Field Effect Transistor

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FEATURES

- 200V , 10A , $R_{DS(ON)}=400m\Omega$ @VGS=10V.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- TO-220 & TO-263 package.



ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous -Pulsed	I_D	10	A
	I_{DM}	40	A
Drain-Source Diode Forward Current	I_S	10	A
Maximum Power Dissipation @ $T_c=25^\circ\text{C}$ Derate above 25°C	P_D	75	W
		0.6	W/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.5	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$

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ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	200			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =160V, V _{GS} =0V			25	μA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS^a						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	2.9	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5A		265	400	mΩ
On-State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} =10V	10			A
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =5A	3	6		S
DYNAMIC CHARACTERISTICS^b						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V f=1.0MHz		646	800	pF
Output Capacitance	C _{OSS}			105	140	pF
Reverse Transfer Capacitance	C _{RSS}			36	50	pF
SWITCHING CHARACTERISTICS^b						
Turn-On Delay Time	t _{D(ON)}	V _{DD} =100V, I _D =5A, V _{GS} =10V, R _{GEN} =50Ω		50	60	ns
Rise Time	t _r			80	120	ns
Turn-Off Delay Time	t _{D(OFF)}			55	80	ns
Fall Time	t _f			40	50	ns
Total Gate Charge	Q _g	V _{DS} =160V, I _D =5.9A, V _{GS} =10V		25	60	nC
Gate-Source Charge	Q _{gs}			5		nC
Gate-Drain Charge	Q _{gd}			7		nC

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ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise noted)

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Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS^a						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_s = 10A$		0.9	1.5	V

Notes

- a. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

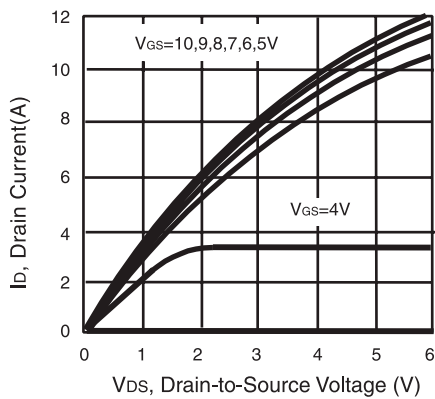


Figure 1. Output Characteristics

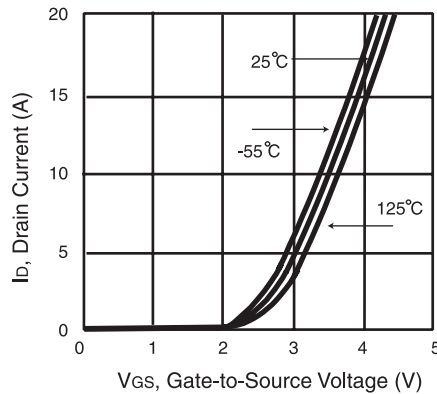


Figure 2. Transfer Characteristics

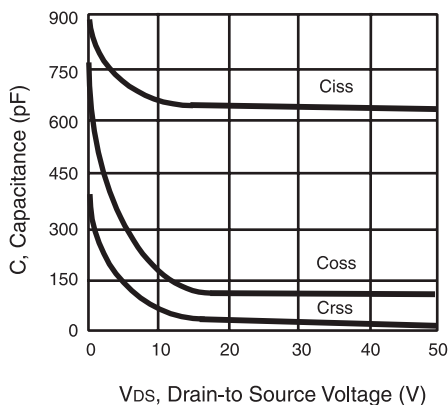


Figure 3. Capacitance

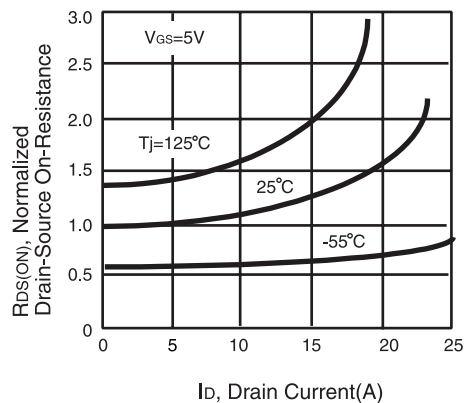


Figure 4. On-Resistance Variation with Drain Current and Temperature

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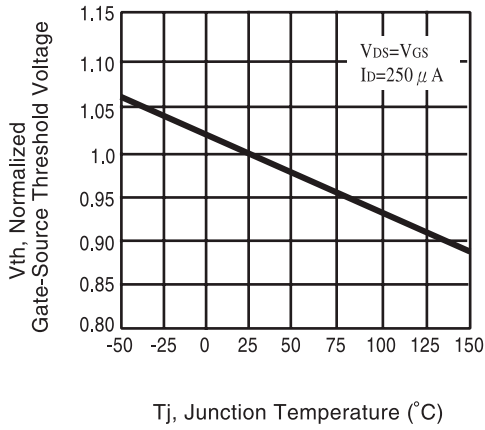


Figure 5. Gate Threshold Variation with Temperature

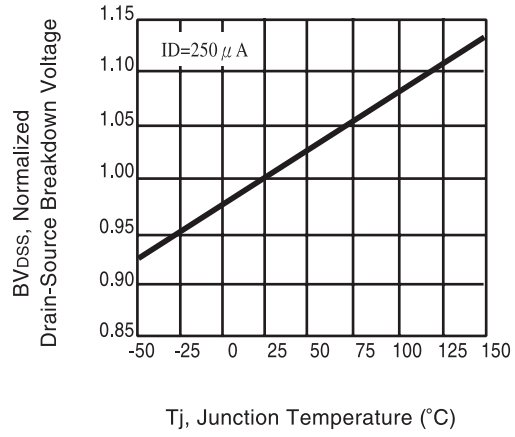


Figure 6. Breakdown Voltage Variation with Temperature

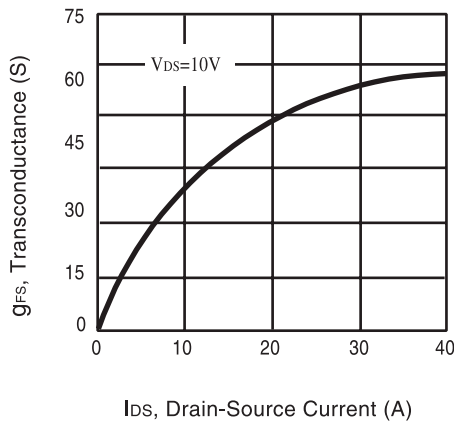


Figure 7. Transconductance Variation with Drain Current

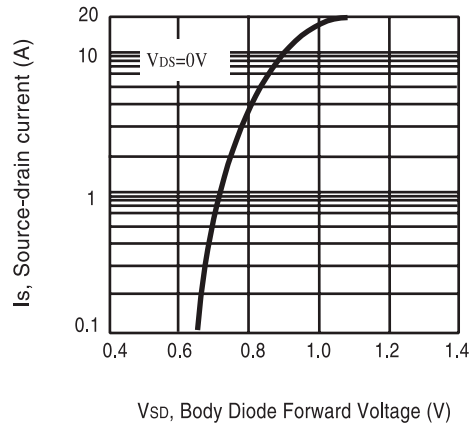


Figure 8. Body Diode Forward Voltage Variation with Source Current

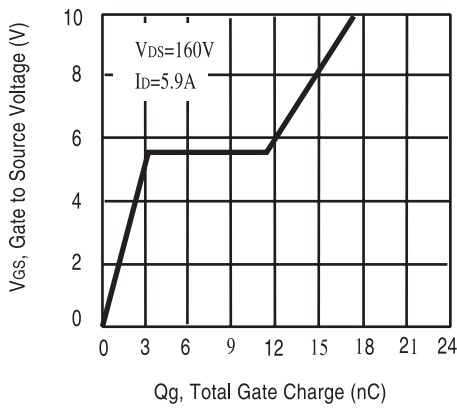


Figure 9. Gate Charge

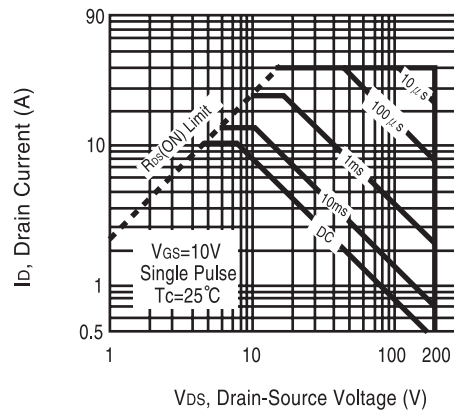


Figure 10. Maximum Safe Operating Area

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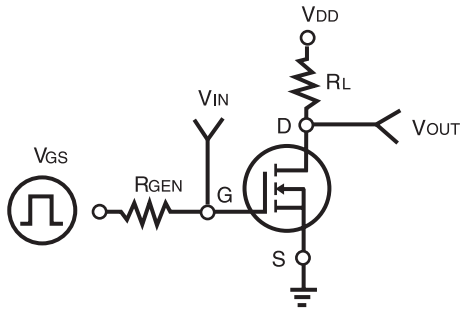


Figure 11. Switching Test Circuit

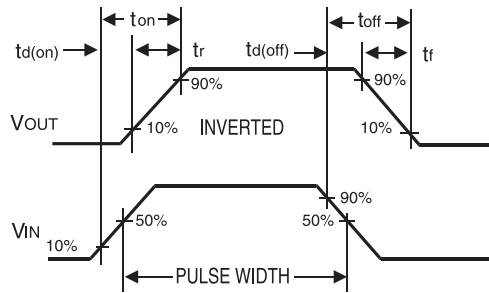


Figure 12. Switching Waveforms

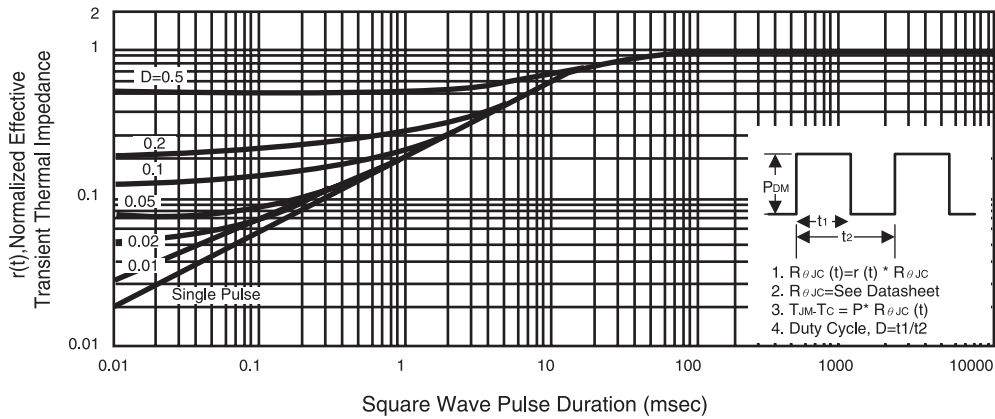


Figure 13. Normalized Thermal Transient Impedance Curve